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Vishay Semiconductors

# ADD-A-PAK Generation VII Power Modules Thyristor/Thyristor, 95 A



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PRODUCT SUMMARY				
I <sub>T(AV)</sub>	95 A			
Type	Modules - Thyristor, Standard			

#### **MECHANICAL DESCRIPTION**

The ADD-A-PAK generation VII, new generation of ADD-A-PAK module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

#### **FEATURES**

- · High voltage
- Industrial standard package



- · Low thermal resistance
- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

#### **BENEFITS**

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- · High surge capability
- · Easy mounting on heatsink

#### **ELECTRICAL DESCRIPTION**

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	VALUES	UNITS		
I <sub>T(AV)</sub>	85 °C	95			
I <sub>T(RMS)</sub>		150	Α		
1	50 Hz	2000	A		
I <sub>TSM</sub>	60 Hz	2094			
I <sup>2</sup> t	50 Hz	20	kA <sup>2</sup> s		
1-1	60 Hz	18.26	KA-5		
I²√t		200	kA²√s		
V <sub>RRM</sub>	Range	400 to 1600	V		
T <sub>Stg</sub>		-40 to 125	°C		
T <sub>J</sub>		-40 to 125	°C		



#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I <sub>RRM,</sub> I <sub>DRM</sub> AT 125 °C mA		
	04	400	500	400			
VS-VSK.91	08	800	900	800	15		
V3-V3N.91	12	1200	1300	1200	15		
	16	1600	1700	1600			

ON-STATE CONDUCTION						
PARAMETER	SYMBOL		TEST COND	ITIONS	VALUES	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	180° conduction T <sub>C</sub> = 85 °C	180° conduction, half sine wave, $T_C = 85$ °C			А
Maximum continuous RMS on-state current		DC			150	
Maximum continuous AMS on-state current	I <sub>T(RMS)</sub>	T <sub>C</sub>		78	°C	
		t = 10 ms	No voltage		2000	
Maximum peak, one-cycle non-repetitive		t = 8.3 ms	reapplied	Sinusoidal	2094	Δ
on-state current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>	half wave, initial $T_J = T_J$ maximum	1682	Α
		t = 8.3 ms	reapplied		1760	
		t = 10 ms	No voltage		20	
10.6.6	l <sup>2</sup> t	t = 8.3 ms	reapplied	Initial $T_J = T_J$ maximum	18.26	kA <sup>2</sup> s
Maximum I <sup>2</sup> t for fusing		t = 10 ms	100 % V <sub>RRM</sub>		14.14	
		t = 8.3 ms	reapplied		12.91	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t <sup>(1)</sup>	$t = 0.1 \text{ ms to } 1000 \text{ ms}$ $T_J = T_J \text{ maximum}$	0 ms, no voltag um	e reapplied	200	kA²√s
	(2)	Low level (3)			0.97	.,
Maximum value of threshold voltage	V <sub>T(TO)</sub> (2)	High level (4)	$T_J = T_J \text{ maxin}$	num	1.1	V
Maximum value of on-state	(2)	Low level (3)	T <sub>J</sub> = T <sub>J</sub> maximum		2.76	mΩ
slope resistance	r <sub>t</sub> <sup>(2)</sup>	High level (4)			2.38	
Maximum on-state voltage drop	$V_{TM}$	$I_{TM} = \pi \times I_{T(AV)}$	$I_{TM} = \pi \times I_{T(AV)}$ $T_J = 25  ^{\circ}C$		1.73	V
Maximum non-repetitive rate of rise of turned on current	dl/dt	$T_J = 25$ °C, from 0.67 $V_{DRM}$ , $I_{TM} = \pi \times I_{T(AV)}$ , $I_g = 500$ mA, $t_r < 0.5$ $\mu s$ , $t_p > 6$ $\mu s$		150	A/µs	
Maximum holding current	I <sub>H</sub>	T <sub>J</sub> = 25 °C, and	T <sub>J</sub> = 25 °C, anode supply = 6 V, resistive load, gate open circuit			mA
Maximum latching current	ΙL	T <sub>J</sub> = 25 °C, and	ode supply = 6 \	/, resistive load	400	

#### Notes

<sup>(1)</sup>  $I^2t$  for time  $t_x = I^2\sqrt{t} \ x \ \sqrt{t_x}$ 

<sup>&</sup>lt;sup>(2)</sup> Average power =  $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$ 

<sup>(3) 16.7 %</sup> x  $\pi$  x  $I_{AV}$  < I <  $\pi$  x  $I_{AV}$ 

 $<sup>^{(4)}~</sup>I>\pi~x~I_{AV}$ 



TRIGGERING						
PARAMETER	PARAMETER SYMBOL		NDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>			12	W	
Maximum average gate power	P <sub>G(AV)</sub>			3.0	VV	
Maximum peak gate current	I <sub>GM</sub>			3.0	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>			10	V	
		T <sub>J</sub> = - 40 °C	Anode supply = 6 V resistive load	4.0		
Maximum gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C		2.5		
		T <sub>J</sub> = 125 °C		1.7		
		T <sub>J</sub> = - 40 °C		270	mA	
Maximum gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	150		
		T <sub>J</sub> = 125 °C		80		
Maximum gate voltage that will not trigger	$V_{GD}$	$V_{GD}$ $T_{J} = 125 ^{\circ}\text{C}$ , rated $V_{DRM}$ applied		0.25	V	
Maximum gate current that will not trigger	I <sub>GD</sub>	$T_J = 125$ °C, rated $V_{DRN}$	<sub>M</sub> applied	6	mA	

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak reverse and off-state leakage current at V <sub>RRM</sub> , V <sub>DRM</sub>	I <sub>RRM,</sub> I <sub>DRM</sub>	T <sub>J</sub> = 125 °C, gate open circuit	15	mA		
Maximum RMS insulation voltage	V <sub>INS</sub>	50 Hz	3000 (1 min) 3600 (1 s)	V		
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J$ = 125 °C, linear to 0.67 $V_{DRM}$	1000	V/µs		

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Junction operating and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-40 to 125	°C	
Maximum internal thermal resistance, junction to case per leg		R <sub>thJC</sub>	DC operation	0.22	°C/W	
Typical thermal resistance, case to heatsink per module		R <sub>thCS</sub>	Mounting surface flat, smooth and greased	0.1	0/ ٧٧	
Mounting torque ± 10 %	to heatsink		A mounting compound is recommended and the torque should be rechecked after a period of	4	Nm	
Woulding torque ± 10 %	busbar		3 hours to allow for the spread of the compound.	3	INIII	
Approximate weight				75	g	
Approximate weight				2.7	OZ.	
Case style			JEDEC®	AAP GEN VI	(TO-240AA)	

△R CONDUCTION PER JUNCTION											
DEVICES	8	SINE HALF WAVE CONDUCTION			RECTANGULAR WAVE CONDUCTION				NC	UNITS	
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSK.91	0.04	0.048	0.063	0.085	0.125	0.033	0.052	0.067	0.088	0.127	°C/W

#### Note

Table shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

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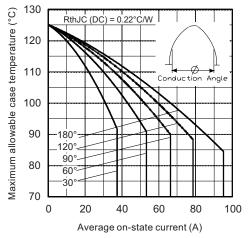


Fig. 1 - Current Ratings Characteristics

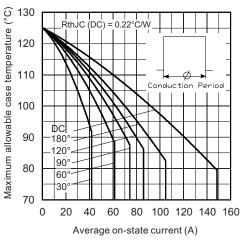


Fig. 2 - Current Ratings Characteristics

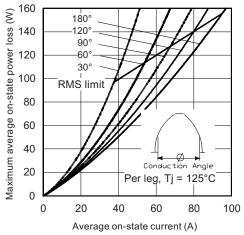


Fig. 3 - On-State Power Loss Characteristics

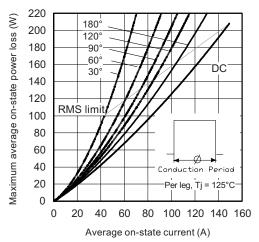


Fig. 4 - On-State Power Loss Characteristics

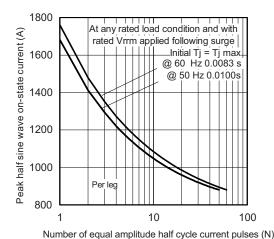


Fig. 5 - Maximum Non-Repetitive Surge Current

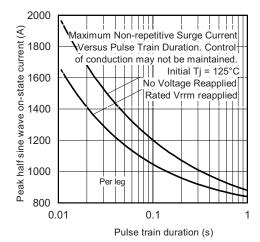


Fig. 6 - Maximum Non-Repetitive Surge Current

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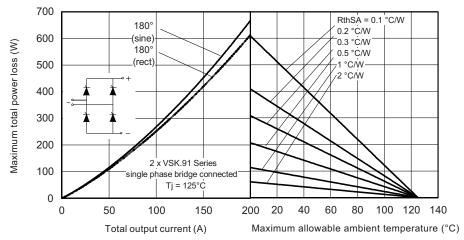


Fig. 7 - On-State Power Loss Characteristics

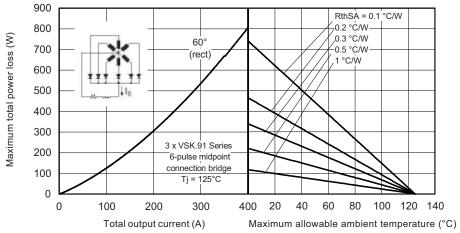


Fig. 8 - On-State Power Loss Characteristics

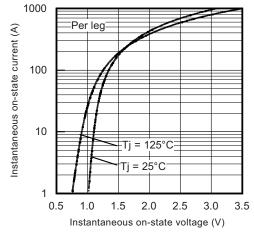


Fig. 9 - On-State Voltage Characteristics

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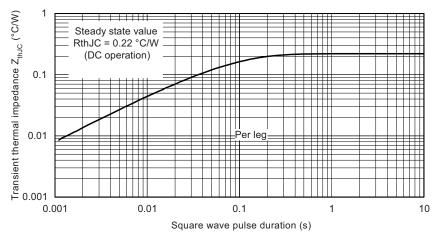
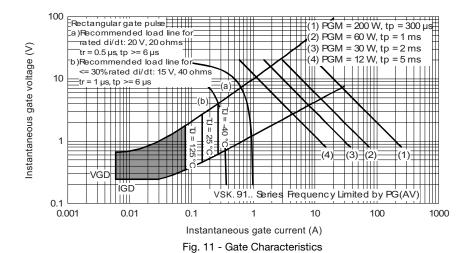
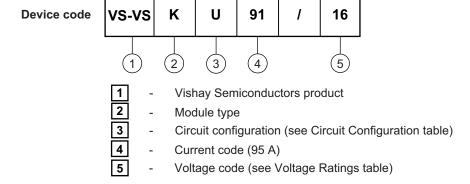


Fig. 10 - Thermal Impedance Z<sub>thJC</sub> Characteristics



### ORDERING INFORMATION TABLE



#### Note

• To order the optional hardware go to <a href="https://www.vishay.com/doc?95172">www.vishay.com/doc?95172</a>



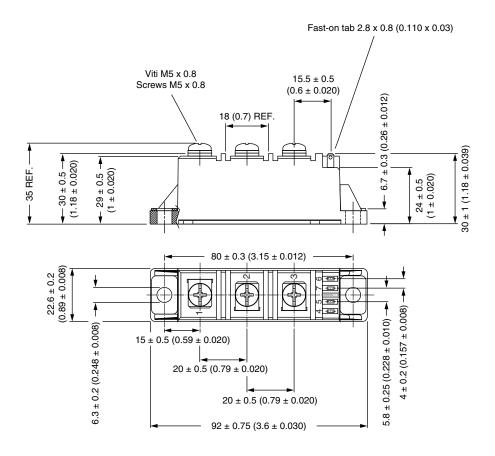
CIRCUIT CONFIGURATION									
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING							
Two SCRs common cathodes	U	VSKU  (1)  1  2  (2)  (3)  (3)  (3)  (4)  (5)  (7)  (6)							
Two SCRs common anodes	V	VSKV  (1)							

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95368			



# **ADD-A-PAK Generation VII - Thyristor**

#### **DIMENSIONS** in millimeters (inches)





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